

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies to 175 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common source amplifier applications in 12.5 volt mobile FM equipment.

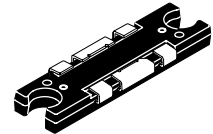
- Specified Performance @ 175 MHz, 12.5 Volts
Output Power — 50 Watts
Power Gain — 14.5 dB
Efficiency — 55%
- Capable of Handling 20:1 VSWR, @ 15.6 Vdc, 175 MHz, 2 dB Overdrive

Features

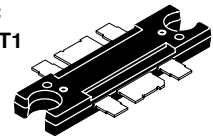
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Broadband-Full Power Across the Band: 135-175 MHz
- 200°C Capable Plastic Package
- N Suffix Indicates Lead-Free Terminations. RoHS Compliant.
- In Tape and Reel. T1 Suffix = 500 Units per 44 mm, 13 inch Reel.

MRF1550NT1
MRF1550FNT1

175 MHz, 50 W, 12.5 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 1264-10, STYLE 1
TO-272-6 WRAP
PLASTIC
MRF1550NT1



CASE 1264A-03, STYLE 1
TO-272-6
PLASTIC
MRF1550FNT1

Table 1. Maximum Ratings

| Rating | Symbol | Value | Unit |
|--|-----------|-------------|--------------------------|
| Drain-Source Voltage | V_{DS} | -0.5, +40 | Vdc |
| Gate-Source Voltage | V_{GS} | ± 20 | Vdc |
| Drain Current — Continuous | I_D | 12 | Adc |
| Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C | P_D | 165 0.50 | W W/ $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -65 to +150 | $^\circ\text{C}$ |
| Operating Junction Temperature | T_J | 200 | $^\circ\text{C}$ |

Table 2. Thermal Characteristics

| Characteristic | Symbol | Value(2) | Unit |
|--------------------------------------|-----------------|----------|---------------------------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 0.75 | $^\circ\text{C}/\text{W}$ |

Table 3. Moisture Sensitivity Level

| Test Methodology | Rating | Package Peak Temperature | Unit |
|--------------------------------------|--------|--------------------------|------------------|
| Per JESD22-A113, IPC/JEDEC J-STD-020 | 3 | 260 | $^\circ\text{C}$ |

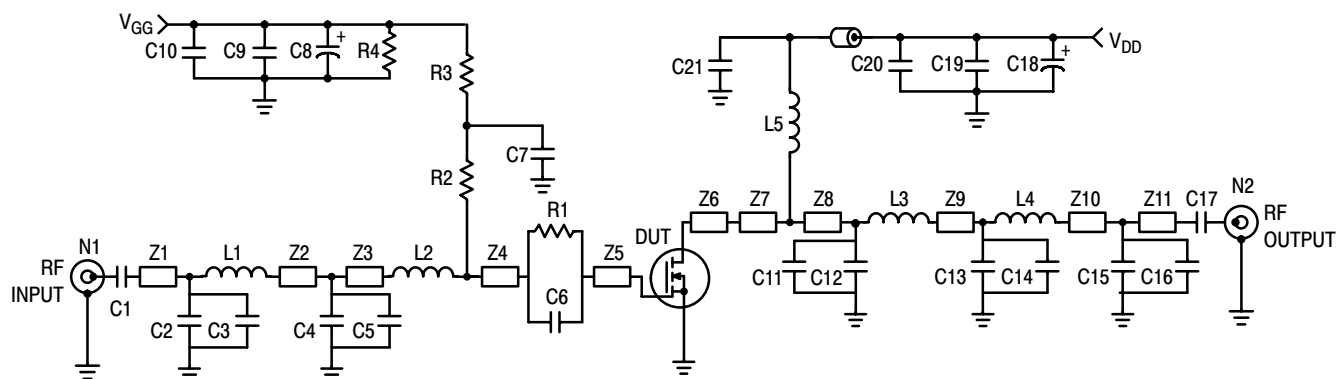
1. Calculated based on the formula $P_D = \frac{T_J - T_C}{R_{\theta JC}}$

2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|--------------|-----|------|-----|--------------------|
| Off Characteristics | | | | | |
| Zero Gate Voltage Drain Current ($V_{DS} = 60\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) | I_{DSS} | — | — | 1 | μA_{dc} |
| Gate-Source Leakage Current ($V_{GS} = 10\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$) | I_{GSS} | — | — | 0.5 | μA_{dc} |
| On Characteristics | | | | | |
| Gate Threshold Voltage ($V_{DS} = 12.5\text{ Vdc}$, $I_D = 800\text{ }\mu\text{A}$) | $V_{GS(th)}$ | 1 | — | 3 | Vdc |
| Drain-Source On-Voltage ($V_{GS} = 5\text{ Vdc}$, $I_D = 1.2\text{ A}$) | $R_{DS(on)}$ | — | — | 0.5 | Ω |
| Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 4.0\text{ Adc}$) | $V_{DS(on)}$ | — | — | 1 | Vdc |
| Dynamic Characteristics | | | | | |
| Input Capacitance (Includes Input Matching Capacitance) ($V_{DS} = 12.5\text{ Vdc}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$) | C_{iss} | — | — | 500 | pF |
| Output Capacitance ($V_{DS} = 12.5\text{ Vdc}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$) | C_{oss} | — | — | 250 | pF |
| Reverse Transfer Capacitance ($V_{DS} = 12.5\text{ Vdc}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$) | C_{rss} | — | — | 35 | pF |
| RF Characteristics (In Freescale Test Fixture) | | | | | |
| Common-Source Amplifier Power Gain ($V_{DD} = 12.5\text{ Vdc}$, $P_{out} = 50\text{ Watts}$, $I_{DQ} = 500\text{ mA}$) $f = 175\text{ MHz}$ | G_{ps} | — | 14.5 | — | dB |
| Drain Efficiency ($V_{DD} = 12.5\text{ Vdc}$, $P_{out} = 50\text{ Watts}$, $I_{DQ} = 500\text{ mA}$) $f = 175\text{ MHz}$ | η | — | 55 | — | % |



| | | | |
|----------|--|--------|-------------------------------------|
| B1 | Ferroxcube #VK200 | L4 | 1 Turn, #26 AWG, 0.240" ID |
| C1 | 180 pF, 100 mil Chip Capacitor | L5 | 3 Turn, #24 AWG, 0.180" ID |
| C2 | 10 pF, 100 mil Chip Capacitor | N1, N2 | Type N Flange Mounts |
| C3 | 33 pF, 100 mil Chip Capacitor | R1 | 5.1 Ω , 1/4 W Chip Resistor |
| C4, C16 | 24 pF, 100 mil Chip Capacitors | R2 | 39 Ω Chip Resistor (0805) |
| C5 | 160 pF, 100 mil Chip Capacitor | R3 | 1 k Ω , 1/8 W Chip Resistor |
| C6 | 240 pF, 100 mil Chip Capacitor | R4 | 33 k Ω , 1/4 W Chip Resistor |
| C7, C17 | 300 pF, 100 mil Chip Capacitors | Z1 | 1.000" x 0.080" Microstrip |
| C8, C18 | 10 μ F, 50 V Electrolytic Capacitors | Z2 | 0.400" x 0.080" Microstrip |
| C9, C19 | 0.1 μ F, 100 mil Chip Capacitors | Z3 | 0.200" x 0.080" Microstrip |
| C10 | 470 pF, 100 mil Chip Capacitor | Z4 | 0.200" x 0.080" Microstrip |
| C11, C12 | 200 pF, 100 mil Chip Capacitors | Z5, Z6 | 0.100" x 0.223" Microstrip |
| C13 | 22 pF, 100 mil Chip Capacitor | Z7 | 0.160" x 0.080" Microstrip |
| C14 | 30 pF, 100 mil Chip Capacitor | Z8 | 0.260" x 0.080" Microstrip |
| C15 | 6.8 pF, 100 mil Chip Capacitor | Z9 | 0.280" x 0.080" Microstrip |
| C20 | 1,000 pF, 100 mil Chip Capacitor | Z10 | 0.270" x 0.080" Microstrip |
| L1 | 18.5 nH, Coilcraft #A05T | Z11 | 0.730" x 0.080" Microstrip |
| L2 | 5 nH, Coilcraft #A02T | Board | Glass Teflon [®] , 31 mils |
| L3 | 1 Turn, #24 AWG, 0.250" ID | | |

Figure 1. 135 - 175 MHz Broadband Test Circuit

TYPICAL CHARACTERISTICS

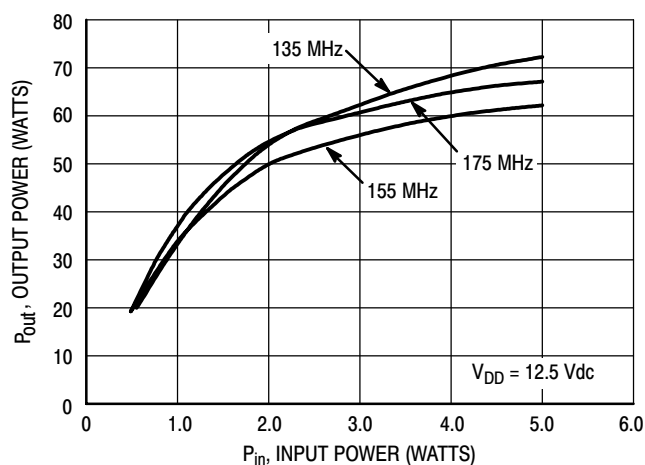


Figure 2. Output Power versus Input Power

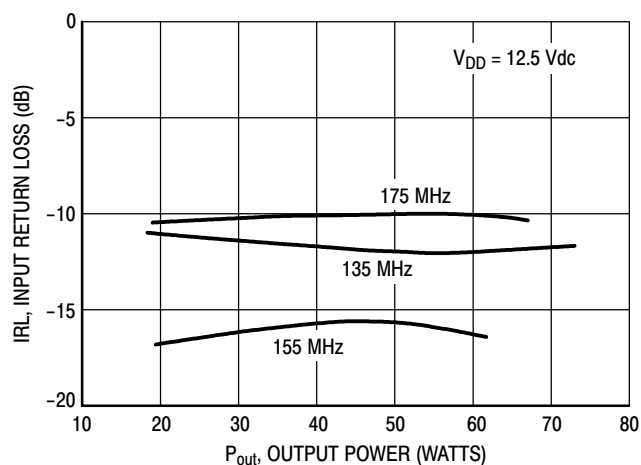


Figure 3. Input Return Loss versus Output Power

TYPICAL CHARACTERISTICS

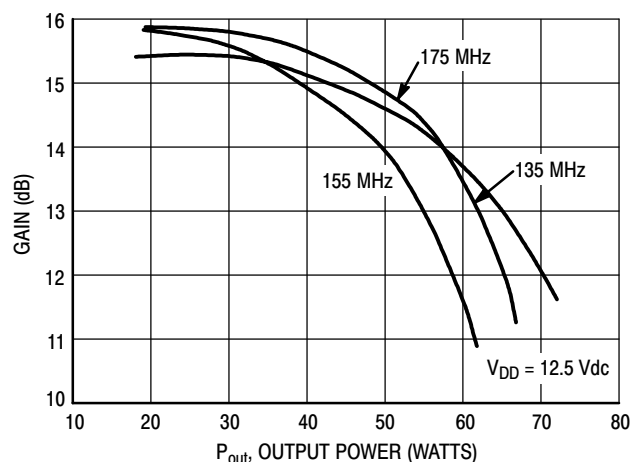


Figure 4. Gain versus Output Power

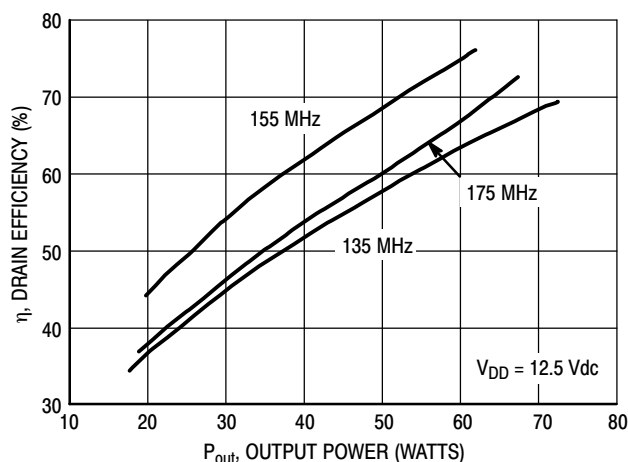


Figure 5. Drain Efficiency versus Output Power

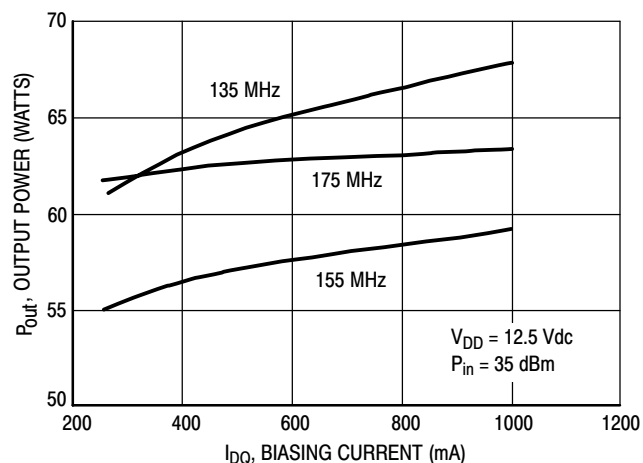


Figure 6. Output Power versus Biasing Current

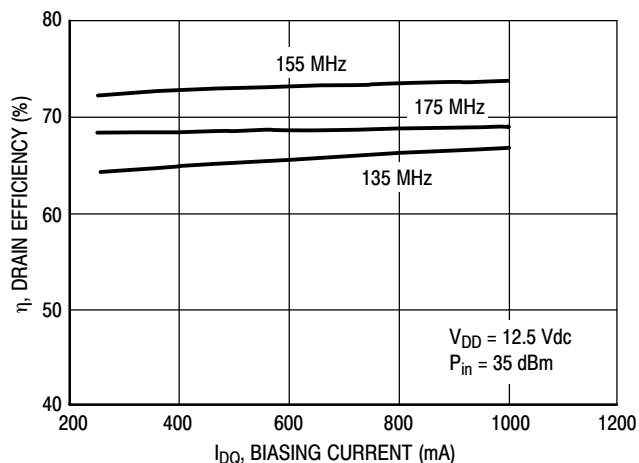


Figure 7. Drain Efficiency versus Biasing Current

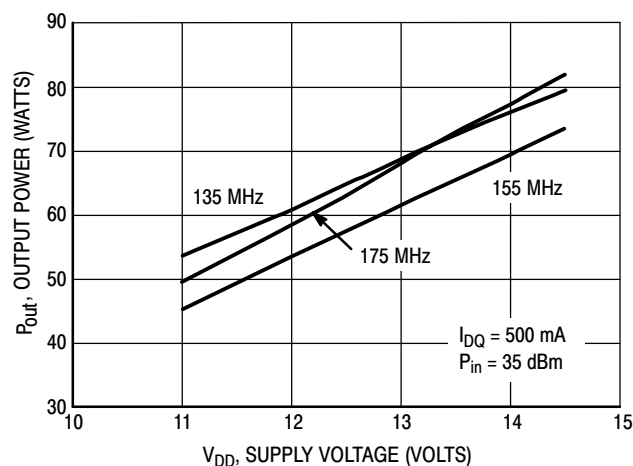


Figure 8. Output Power versus Supply Voltage

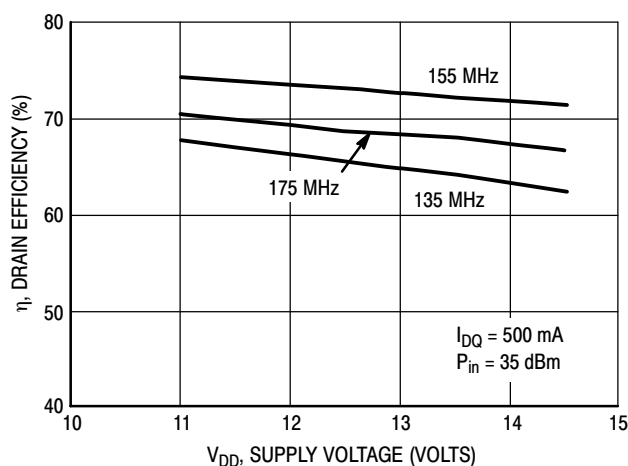
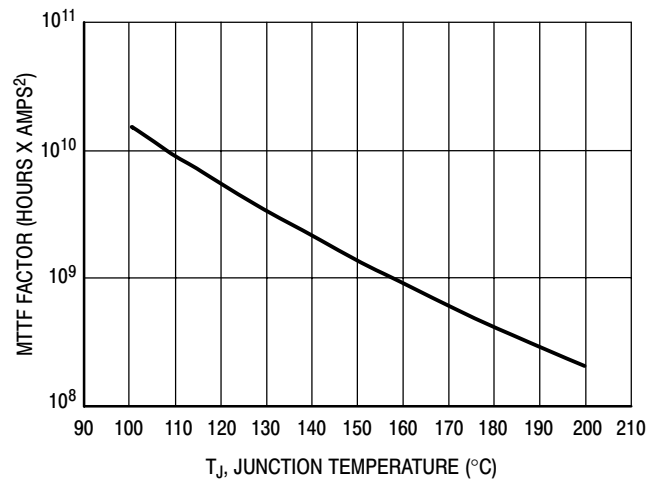


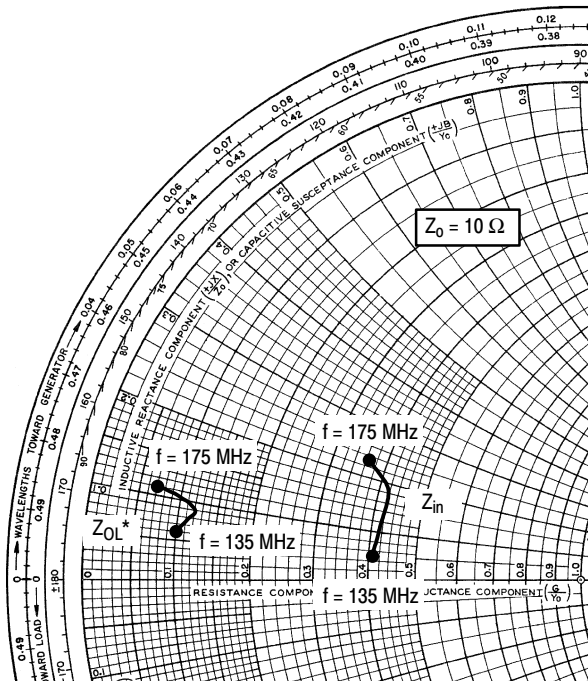
Figure 9. Drain Efficiency versus Supply Voltage

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than $\pm 10\%$ of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 10. MTTF Factor versus Junction Temperature



$V_{DD} = 12.5 \text{ V}$, $I_{DQ} = 500 \text{ mA}$, $P_{out} = 50 \text{ W}$

| f MHz | Z_{in} Ω | Z_{OL}^* Ω |
|----------|----------------------|------------------------|
| 135 | $4.1 + j0.5$ | $1.0 + j0.6$ |
| 155 | $4.2 + j1.7$ | $1.2 + j0.9$ |
| 175 | $3.7 + j2.3$ | $0.7 + j1.1$ |

Z_{in} = Complex conjugate of source impedance.

Z_{OL}^* = Complex conjugate of the load impedance at given output power, voltage, frequency, and $\eta_D > 50 \%$.

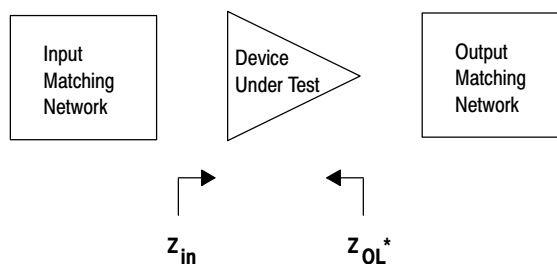


Figure 11. Series Equivalent Input and Output Impedance

Table 5. Common Source Scattering Parameters ($V_{DD} = 12.5$ Vdc)
 $I_{DQ} = 500$ mA

| f MHz | S ₁₁ | | S ₂₁ | | S ₁₂ | | S ₂₂ | |
|----------|-----------------|------|-----------------|-----|-----------------|-----|-----------------|------|
| | S ₁₁ | ∠ φ | S ₂₁ | ∠ φ | S ₁₂ | ∠ φ | S ₂₂ | ∠ φ |
| 50 | 0.93 | -178 | 4.817 | 80 | 0.009 | -39 | 0.86 | -176 |
| 100 | 0.94 | -178 | 2.212 | 69 | 0.009 | -3 | 0.88 | -175 |
| 150 | 0.95 | -178 | 1.349 | 61 | 0.008 | -8 | 0.90 | -174 |
| 200 | 0.95 | -178 | 0.892 | 54 | 0.006 | -13 | 0.92 | -174 |
| 250 | 0.96 | -178 | 0.648 | 51 | 0.005 | -7 | 0.93 | -174 |
| 300 | 0.97 | -178 | 0.481 | 47 | 0.004 | -8 | 0.95 | -174 |
| 350 | 0.97 | -178 | 0.370 | 46 | 0.005 | 4 | 0.95 | -174 |
| 400 | 0.98 | -178 | 0.304 | 43 | 0.001 | 15 | 0.97 | -174 |
| 450 | 0.98 | -178 | 0.245 | 43 | 0.005 | 81 | 0.97 | -174 |
| 500 | 0.98 | -178 | 0.209 | 43 | 0.003 | 84 | 0.97 | -174 |
| 550 | 0.99 | -177 | 0.178 | 41 | 0.007 | 70 | 0.98 | -175 |
| 600 | 0.98 | -178 | 0.149 | 41 | 0.010 | 106 | 0.96 | -175 |

 $I_{DQ} = 2.0$ mA

| f MHz | S ₁₁ | | S ₂₁ | | S ₁₂ | | S ₂₂ | |
|----------|-----------------|------|-----------------|-----|-----------------|------|-----------------|------|
| | S ₁₁ | ∠ φ | S ₂₁ | ∠ φ | S ₁₂ | ∠ φ | S ₂₂ | ∠ φ |
| 50 | 0.93 | -177 | 4.81 | 80 | 0.003 | -119 | 0.93 | -178 |
| 100 | 0.94 | -178 | 2.20 | 69 | 0.006 | 4 | 0.93 | -178 |
| 150 | 0.95 | -178 | 1.35 | 61 | 0.003 | -1 | 0.93 | -177 |
| 200 | 0.95 | -178 | 0.89 | 54 | 0.004 | 18 | 0.93 | -176 |
| 250 | 0.96 | -178 | 0.65 | 51 | 0.001 | 28 | 0.94 | -176 |
| 300 | 0.97 | -178 | 0.48 | 47 | 0.004 | 77 | 0.94 | -175 |
| 350 | 0.97 | -178 | 0.37 | 46 | 0.006 | 85 | 0.95 | -175 |
| 400 | 0.98 | -178 | 0.30 | 43 | 0.007 | 53 | 0.96 | -174 |
| 450 | 0.98 | -178 | 0.25 | 43 | 0.006 | 74 | 0.97 | -174 |
| 500 | 0.98 | -177 | 0.21 | 44 | 0.006 | 84 | 0.97 | -174 |
| 550 | 0.99 | -177 | 0.18 | 41 | 0.002 | 106 | 0.97 | -175 |
| 600 | 0.98 | -178 | 0.15 | 41 | 0.004 | 116 | 0.96 | -174 |

 $I_{DQ} = 4.0$ mA

| f MHz | S ₁₁ | | S ₂₁ | | S ₁₂ | | S ₂₂ | |
|----------|-----------------|------|-----------------|-----|-----------------|------|-----------------|------|
| | S ₁₁ | ∠ φ | S ₂₁ | ∠ φ | S ₁₂ | ∠ φ | S ₂₂ | ∠ φ |
| 50 | 0.97 | -179 | 5.04 | 87 | 0.002 | -116 | 0.94 | -179 |
| 100 | 0.96 | -179 | 2.43 | 82 | 0.006 | 42 | 0.94 | -178 |
| 150 | 0.96 | -179 | 1.60 | 77 | 0.004 | 13 | 0.94 | -177 |
| 200 | 0.96 | -179 | 1.14 | 74 | 0.003 | 43 | 0.95 | -176 |
| 250 | 0.97 | -179 | 0.89 | 71 | 0.004 | 65 | 0.95 | -175 |
| 300 | 0.97 | -179 | 0.71 | 68 | 0.006 | 68 | 0.95 | -175 |
| 350 | 0.97 | -179 | 0.57 | 67 | 0.006 | 74 | 0.97 | -174 |

(continued)

Table 5. Common Source Scattering Parameters ($V_{DD} = 12.5$ Vdc) (continued)

$I_{DQ} = 4.0$ mA (continued)

| f MHz | S₁₁ | | S₂₁ | | S₁₂ | | S₂₂ | |
|------------------------|-------------------------|------------|-------------------------|------------|-------------------------|------------|-------------------------|------------|
| | S₁₁ | ∠ φ | S₂₁ | ∠ φ | S₁₂ | ∠ φ | S₂₂ | ∠ φ |
| 400 | 0.97 | -179 | 0.49 | 63 | 0.005 | 58 | 0.97 | -173 |
| 450 | 0.98 | -178 | 0.41 | 63 | 0.005 | 73 | 0.98 | -173 |
| 500 | 0.98 | -178 | 0.36 | 62 | 0.003 | 128 | 0.98 | -173 |
| 550 | 0.98 | -178 | 0.32 | 58 | 0.004 | 57 | 0.99 | -174 |
| 600 | 0.98 | -178 | 0.27 | 58 | 0.009 | 83 | 0.98 | -174 |

DESIGN CONSIDERATIONS

This device is a common-source, RF power, N-Channel enhancement mode, Lateral Metal-Oxide Semiconductor Field-Effect Transistor (MOSFET). Freescale Application Note AN211A, "FETs in Theory and Practice", is suggested reading for those not familiar with the construction and characteristics of FETs.

This surface mount packaged device was designed primarily for VHF and UHF mobile power amplifier applications. Manufacturability is improved by utilizing the tape and reel capability for fully automated pick and placement of parts. However, care should be taken in the design process to insure proper heat sinking of the device.

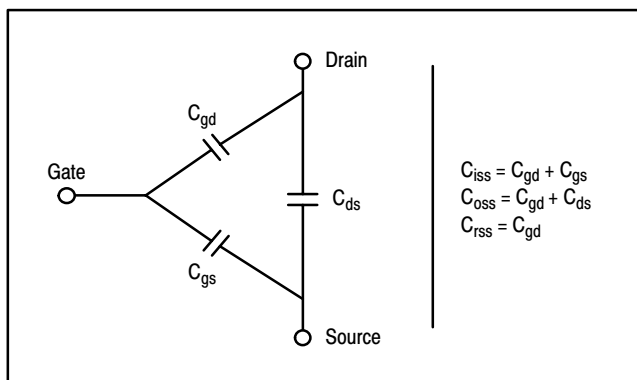
The major advantages of Lateral RF power MOSFETs include high gain, simple bias systems, relative immunity from thermal runaway, and the ability to withstand severely mismatched loads without suffering damage.

MOSFET CAPACITANCES

The physical structure of a MOSFET results in capacitors between all three terminals. The metal oxide gate structure determines the capacitors from gate-to-drain (C_{gd}), and gate-to-source (C_{gs}). The PN junction formed during fabrication of the RF MOSFET results in a junction capacitance from drain-to-source (C_{ds}). These capacitances are characterized as input (C_{iss}), output (C_{oss}) and reverse transfer (C_{rss}) capacitances on data sheets. The relationships between the inter-terminal capacitances and those given on data sheets are shown below. The C_{iss} can be specified in two ways:

1. Drain shorted to source and positive voltage at the gate.
2. Positive voltage of the drain in respect to source and zero volts at the gate.

In the latter case, the numbers are lower. However, neither method represents the actual operating conditions in RF applications.



DRAIN CHARACTERISTICS

One critical figure of merit for a FET is its static resistance in the full-on condition. This on-resistance, $R_{DS(on)}$, occurs in the linear region of the output characteristic and is specified at a specific gate-source voltage and drain current. The

drain-source voltage under these conditions is termed $V_{DS(on)}$. For MOSFETs, $V_{DS(on)}$ has a positive temperature coefficient at high temperatures because it contributes to the power dissipation within the device.

BV_{DSS} values for this device are higher than normally required for typical applications. Measurement of BV_{DSS} is not recommended and may result in possible damage to the device.

GATE CHARACTERISTICS

The gate of the RF MOSFET is a polysilicon material, and is electrically isolated from the source by a layer of oxide. The DC input resistance is very high - on the order of $10^9 \Omega$ — resulting in a leakage current of a few nanoamperes.

Gate control is achieved by applying a positive voltage to the gate greater than the gate-to-source threshold voltage, $V_{GS(th)}$.

Gate Voltage Rating — Never exceed the gate voltage rating. Exceeding the rated V_{GS} can result in permanent damage to the oxide layer in the gate region.

Gate Termination — The gates of these devices are essentially capacitors. Circuits that leave the gate open-circuited or floating should be avoided. These conditions can result in turn-on of the devices due to voltage build-up on the input capacitor due to leakage currents or pickup.

Gate Protection — These devices do not have an internal monolithic zener diode from gate-to-source. If gate protection is required, an external zener diode is recommended. Using a resistor to keep the gate-to-source impedance low also helps dampen transients and serves another important function. Voltage transients on the drain can be coupled to the gate through the parasitic gate-drain capacitance. If the gate-to-source impedance and the rate of voltage change on the drain are both high, then the signal coupled to the gate may be large enough to exceed the gate-threshold voltage and turn the device on.

DC BIAS

Since this device is an enhancement mode FET, drain current flows only when the gate is at a higher potential than the source. RF power FETs operate optimally with a quiescent drain current (I_{DQ}), whose value is application dependent. This device was characterized at $I_{DQ} = 500 \text{ mA}$, which is the suggested value of bias current for typical applications. For special applications such as linear amplification, I_{DQ} may have to be selected to optimize the critical parameters.

The gate is a dc open circuit and draws no current. Therefore, the gate bias circuit may generally be just a simple resistive divider network. Some special applications may require a more elaborate bias system.

GAIN CONTROL

Power output of this device may be controlled to some degree with a low power dc control signal applied to the gate, thus facilitating applications such as manual gain control, ALC/AGC and modulation systems. This characteristic is very dependent on frequency and load line.

AMPLIFIER DESIGN

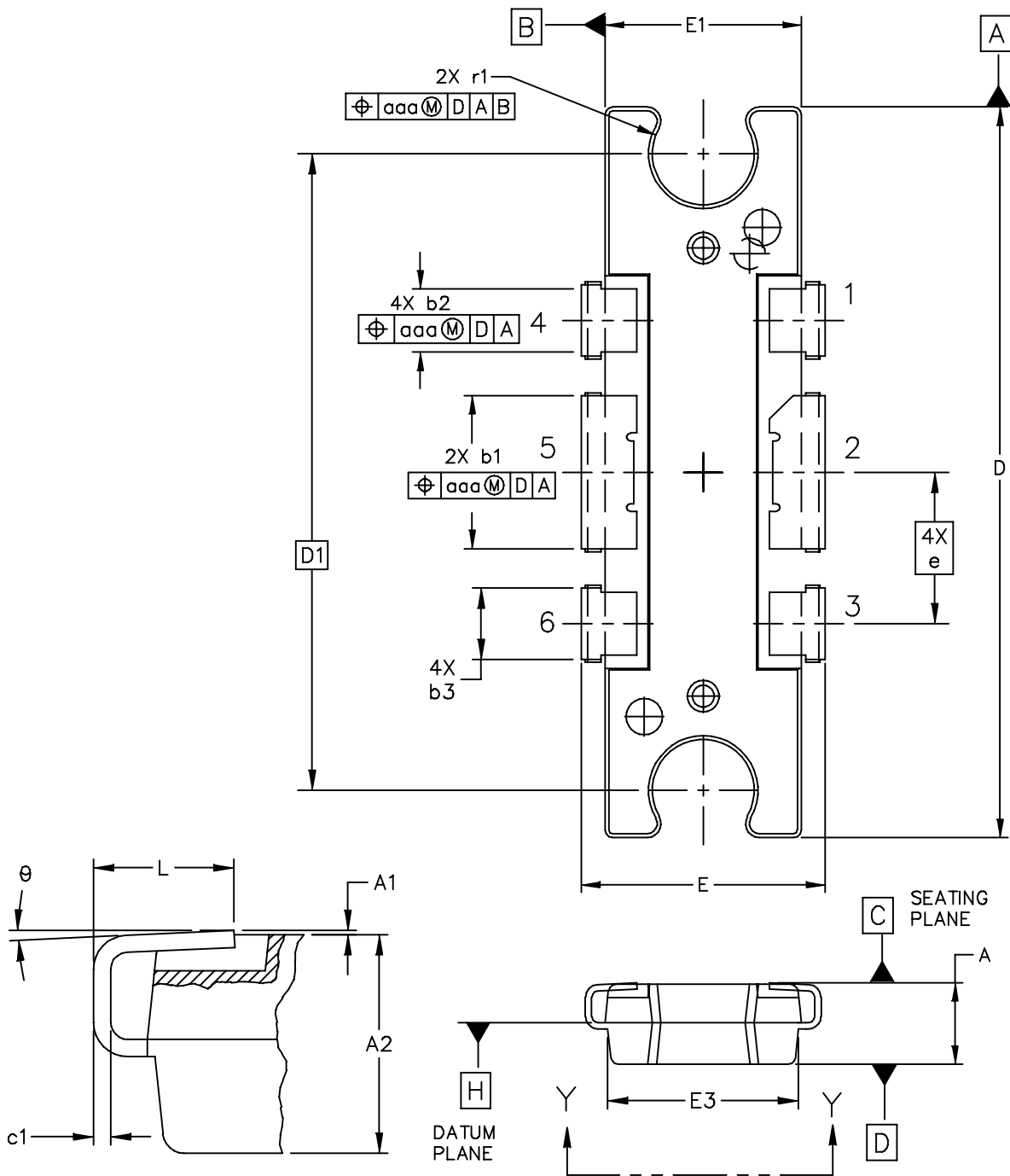
Impedance matching networks similar to those used with bipolar transistors are suitable for this device. For examples see Freescale Application Note AN721, "Impedance Matching Networks Applied to RF Power Transistors." Large-signal impedances are provided, and will yield a good first pass approximation.

Since RF power MOSFETs are triode devices, they are not unilateral. This coupled with the very high gain of this device yields a device capable of self oscillation. Stability may be achieved by techniques such as drain loading, input shunt

resistive loading, or output to input feedback. The RF test fixture implements a parallel resistor and capacitor in series with the gate, and has a load line selected for a higher efficiency, lower gain, and more stable operating region.

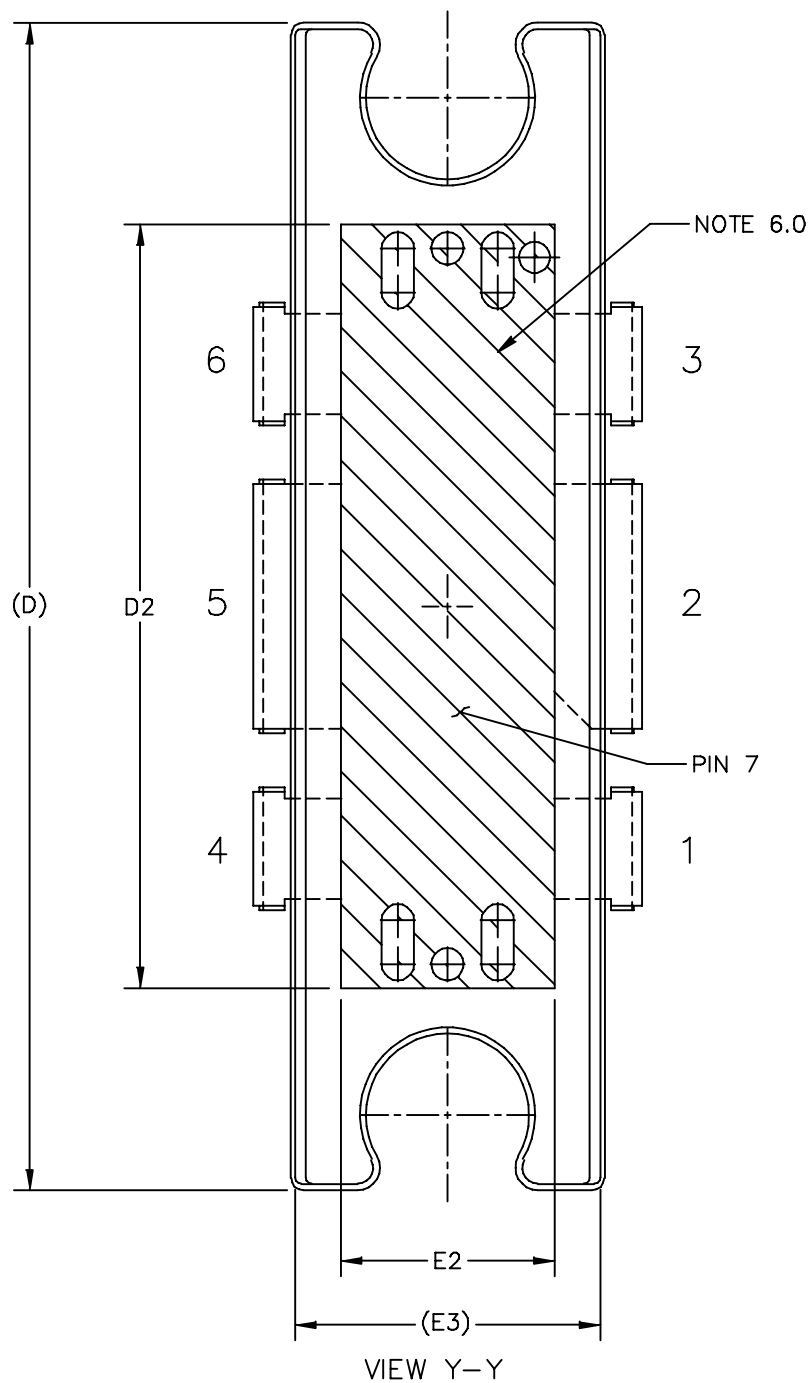
Two-port stability analysis with this device's S-parameters provides a useful tool for selection of loading or feedback circuitry to assure stable operation. See Freescale Application Note AN215A, "RF Small-Signal Design Using Two-Port Parameters" for a discussion of two port network theory and stability.

PACKAGE DIMENSIONS



| | | | |
|---|--------------------|----------------------------|-------------|
| © FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED. | MECHANICAL OUTLINE | PRINT VERSION NOT TO SCALE | |
| TITLE: TO-272 SCREW DOWN MOUNT | | DOCUMENT NO: 98ASH98116A | REV: L |
| | | CASE NUMBER: 1264-10 | 03 AUG 2007 |
| | | STANDARD: JEDEC TO-272 AA | |

MRF1550NT1 MRF1550FNT1



| | | | |
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| TITLE: TO-272 SCREW DOWN MOUNT | | DOCUMENT NO: 98ASH98116A | REV: L |
| | | CASE NUMBER: 1264-10 | 03 AUG 2007 |
| | | STANDARD: JEDEC TO-272 AA | |

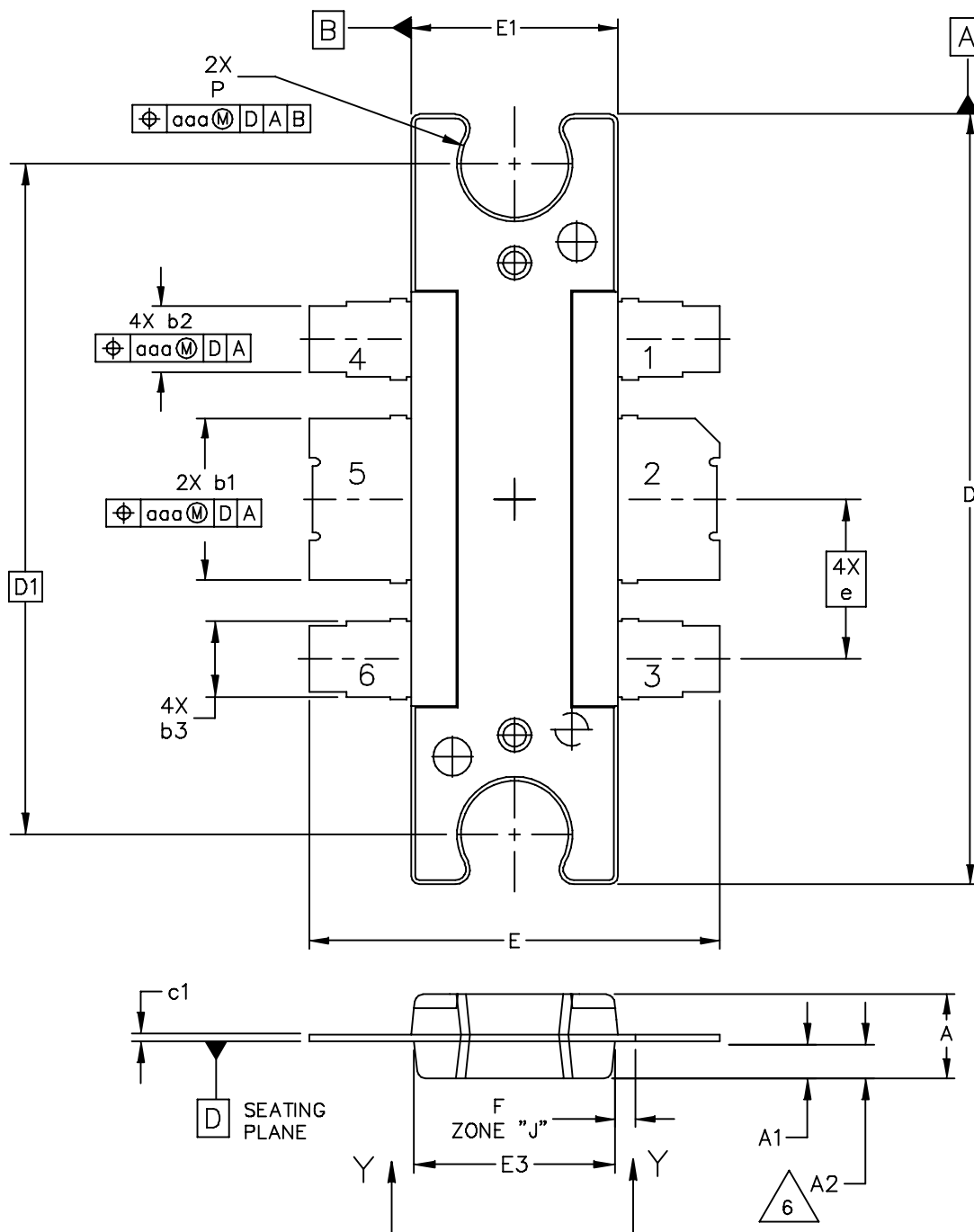
NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSIONS "b1" AND "b3" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" AND "b2" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
6. CROSSHATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

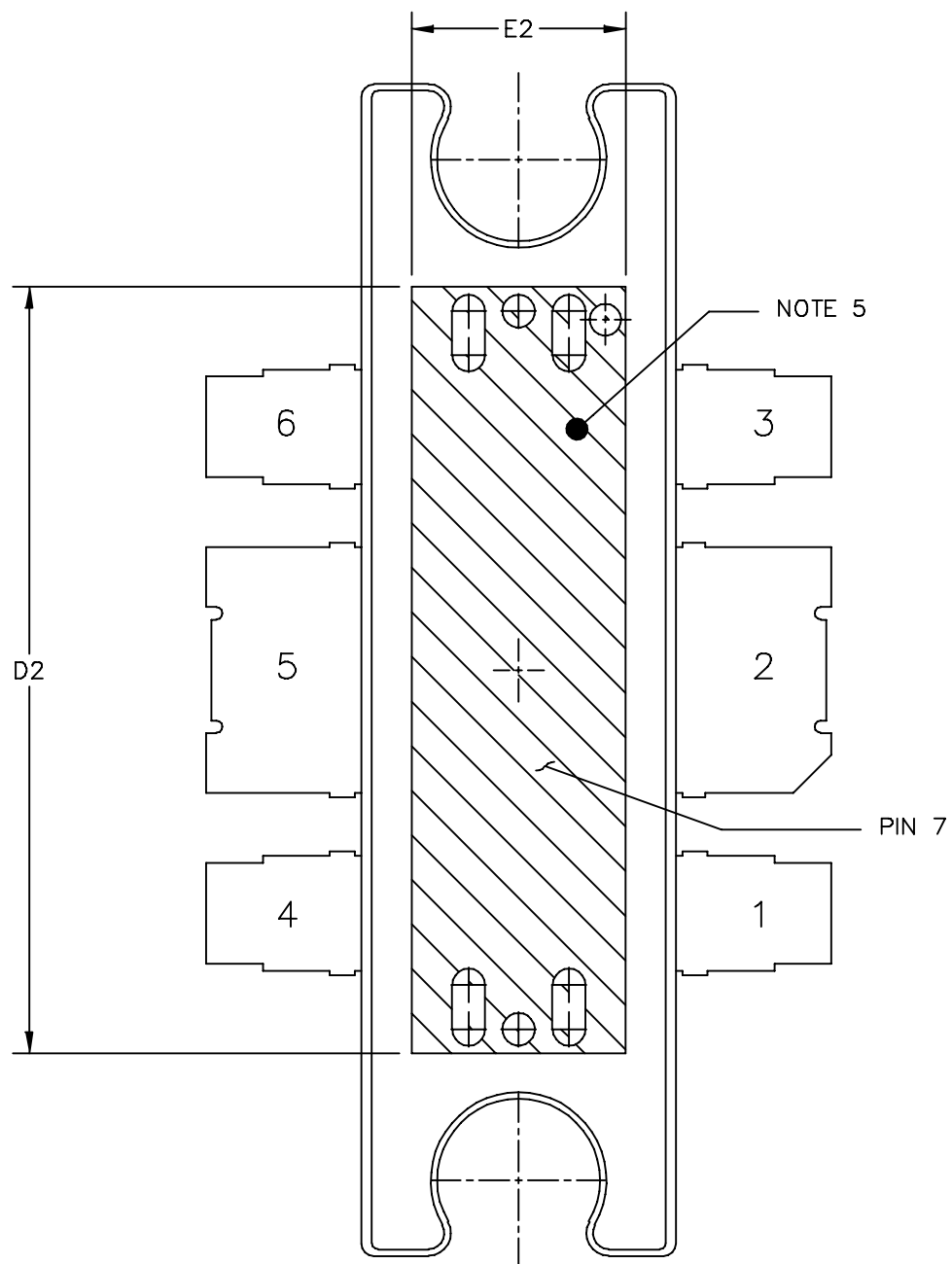
STYLE 1:

| | |
|-------------------------|-------------------------|
| PIN 1 - SOURCE (COMMON) | PIN 4 - SOURCE (COMMON) |
| PIN 2 - DRAIN | PIN 5 - GATE |
| PIN 3 - SOURCE (COMMON) | PIN 6 - SOURCE (COMMON) |
| | PIN 7 - SOURCE (COMMON) |

| INCH | | | MILLIMETER | | INCH | | | MILLIMETER | |
|---|------|------|--------------------|-------|---------------------------|----------------------------|------|-------------|------|
| DIM | MIN | MAX | MIN | MAX | DIM | MIN | MAX | MIN | MAX |
| A | .098 | .108 | 2.49 | 2.74 | b1 | .193 | .199 | 4.90 | 5.05 |
| A1 | .000 | .004 | 0.00 | 0.10 | b2 | .078 | .084 | 1.98 | 2.13 |
| A2 | .100 | .104 | 2.54 | 2.64 | b3 | .088 | .094 | 2.24 | 2.39 |
| D | .928 | .932 | 23.57 | 23.67 | c1 | .007 | .011 | 0.18 | 0.28 |
| D1 | .806 | .814 | 20.47 | 20.68 | e | .193 BSC | | 4.90 BSC | |
| D2 | .604 | ---- | 15.34 | ---- | r1 | .063 | .068 | 1.60 | 1.73 |
| E | .296 | .304 | 7.52 | 7.72 | θ | 0° | 6° | 0° | 6° |
| E1 | .248 | .252 | 6.30 | 6.40 | aaa | .004 | | 0.1 | |
| E2 | .162 | ---- | 4.11 | ---- | | | | | |
| E3 | .241 | .245 | 6.12 | 6.22 | | | | | |
| L | .060 | .070 | 1.52 | 1.78 | | | | | |
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| TITLE: TO-272 SCREW DOWN MOUNT | | | | | DOCUMENT NO: 98ASH98116A | | | REV: L | |
| | | | | | CASE NUMBER: 1264-10 | | | 03 AUG 2007 | |
| | | | | | STANDARD: JEDEC TO-272 AA | | | | |



| | | | |
|---|---------------------------|--------------------|----------------------------|
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| TITLE: TO-272, 6 LEAD PLASTIC | DOCUMENT NO: 98ASA10536D | | REV: D |
| | CASE NUMBER: 1264A-03 | | 03 AUG 2007 |
| | STANDARD: JEDEC TO-272 BA | | |



VIEW Y-Y

| | | | |
|---|---------------------------|----------------------------|-------------|
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| TITLE: TO-272, 6 LEAD PLASTIC | DOCUMENT NO: 98ASA10536D | | REV: D |
| | CASE NUMBER: 1264A-03 | | 03 AUG 2007 |
| | STANDARD: JEDEC TO-272 BA | | |

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
4. DIMENSIONS "b1" AND "b3" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" AND "b2" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
5. CROSSHATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.
6. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.

STYLE 1:

| | |
|-------------------------|-------------------------|
| PIN 1 - SOURCE (COMMON) | PIN 4 - SOURCE (COMMON) |
| PIN 2 - DRAIN | PIN 5 - GATE |
| PIN 3 - SOURCE (COMMON) | PIN 6 - SOURCE (COMMON) |
| | PIN 7 - SOURCE (COMMON) |

| INCH | | | MILLIMETER | | INCH | | | MILLIMETER | |
|---|----------|------|--------------------|-------|---------------------------|----------------------------|------|-------------|------|
| DIM | MIN | MAX | MIN | MAX | DIM | MIN | MAX | MIN | MAX |
| A | .098 | .106 | 2.49 | 2.69 | b1 | .193 | .199 | 4.90 | 5.05 |
| A1 | .038 | .044 | 0.96 | 1.12 | b2 | .078 | .084 | 1.98 | 2.13 |
| A2 | .040 | .042 | 1.02 | 1.07 | b3 | .088 | .094 | 2.24 | 2.39 |
| D | .926 | .934 | 23.52 | 23.72 | c1 | .007 | .011 | .178 | .279 |
| D1 | .810 BSC | | 20.57 BSC | | e | .193 BSC | | 4.90 BSC | |
| D2 | .604 | ---- | 15.34 | ---- | aaa | .004 | | 0.1 | |
| E | .492 | .500 | 12.50 | 12.70 | | | | | |
| E1 | .246 | .254 | 6.25 | 6.45 | | | | | |
| E2 | .162 | ---- | 4.11 | ---- | | | | | |
| E3 | .241 | .245 | 6.12 | 6.22 | | | | | |
| F | .025 BSC | | 0.64 BSC | | | | | | |
| P | .126 | .134 | 3.20 | 3.40 | | | | | |
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| TITLE: TO-272, 6 LEAD PLASTIC | | | | | DOCUMENT NO: 98ASA10536D | | | REV: D | |
| | | | | | CASE NUMBER: 1264A-03 | | | 03 AUG 2007 | |
| | | | | | STANDARD: JEDEC TO-272 BA | | | | |

PRODUCT DOCUMENTATION, TOOLS AND SOFTWARE

Refer to the following documents to aid your design process.

Application Notes

- AN211A: Field Effect Transistors in Theory and Practice
- AN215A: RF Small-Signal Design Using Two-Port Parameters
- AN721: Impedance Matching Networks Applied to RF Power Transistors
- AN1907: Solder Reflow Attach Method for High Power RF Devices in Plastic Packages
- AN3263: Bolt Down Mounting Method for High Power RF Transistors and RFICs in Over-Molded Plastic Packages
- AN3789: Clamping of High Power RF Transistors and RFICs in Over-Molded Plastic Packages

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator

For Software and Tools, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

| Revision | Date | Description |
|----------|-----------|--|
| 12 | Feb. 2008 | <ul style="list-style-type: none">• Changed DC Bias I_{DQ} value from 150 to 500 to match Functional Test I_{DQ} specification, p. 9• Replaced Case Outline 1264-09 with 1264-10, Issue L, p. 1, 11-13. Removed Drain-ID label from top view and View Y-Y. Corrected cross hatch pattern and its dimensions (D2 and E2) on source contact. Renamed E2 with E3. Added Pin 7 designation. Corrected positional tolerance for bolt hole radius. Added JEDEC Standard Package Number.• Replaced Case Outline 1264A-02 with 1264A-03, Issue D, p. 1, 14-16. Removed Drain-ID label from View Y-Y. Corrected cross hatch pattern and its dimensions (D2 and E2) on source contact (Changed D2 and E2 dimensions from basic to .604 Min and .162 Min, respectively). Added dimension E3. Added Pin 7 designation. Corrected positional tolerance for bolt hole radius. Added JEDEC Standard Package Number.• Added Product Documentation and Revision History, p. 17 |
| 13 | June 2008 | <ul style="list-style-type: none">• Corrected specified performance values for power gain and efficiency on p. 1 to match typical performance values in the functional test table on p. 2 |
| 14 | Oct. 2008 | <ul style="list-style-type: none">• Corrected 155 MHz Z_{OL} value and replotted data, Fig. 11, Series Equivalent Input and Output Impedance, p. 6 |
| 15 | June 2009 | <ul style="list-style-type: none">• Modified data sheet to reflect MSL rating change from 1 to 3 as a result of the standardization of packing process as described in Product and Process Change Notification number, PCN13516, p. 1• Added AN3789, Clamping of High Power RF Transistors and RFICs in Over-Molded Plastic Packages to Product Documentation, Application Notes, p. 17• Added Electromigration MTTF Calculator availability to Product Software, p. 17 |

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